

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions and listings of claims in the application:

Claim 1 (currently amended): An etching method for etching an etching target film formed on a substrate an SiO<sub>2</sub> placed inside an airtight processing chamber by inducing a processing gas into said processing chamber, wherein;

said processing gas contains N<sub>2</sub> and at least one of C<sub>4</sub>F<sub>8</sub> and CF<sub>4</sub>; and  
said etching target film is an upper organic film containing Si formed on an SiO<sub>2</sub> film.

Claim 2 (original): An etching method according to claim 1, wherein:

said organic film containing Si is constituted of SiO<sub>2</sub> containing C and H.

Claim 3 (original): An etching method according to claim 1, wherein:

the dielectric constant of said organic film containing Si is equal to or lower than 3.0.

Claim 4 (original): An etching method according to claim 1, wherein:

said organic film containing Si is an organic polysiloxane film.

Claim 5 (original): An etching method according to claim 1, wherein:

said processing gas further contains Ar.

Claims 6-12 (canceled).

Claim 13 (previously presented): An etching method according to claim 1,  
wherein;

said processing gas contains at least CF<sub>4</sub> and N<sub>2</sub>.

Claim 14 (previously presented): An etching method according to claim 13,  
wherein; the flow rate ratio of CF<sub>4</sub> and N<sub>2</sub> in said processing gas is essentially set within  
a range of  $1 \leq (\text{N}_2 \text{ flow rate} / \text{CF}_4 \text{ flow rate}) \leq 4$ .

Claims 15 and 16 (canceled).

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